

ABSTRACT OF THE DISCLOSURE

The invention relates to a process for patterning dielectric layers. A photoresist layer is applied to the dielectric layer and patterned. Then, the pattern which has been predetermined by the resist mask is transferred to the dielectric layer. The incineration of the resist mask is carried out at a temperature of 50°C to 200°C, with the oxygen plasma being generated from a gas which has an oxygen content of 40 to 60% by volume. During a subsequent step of cleaning the patterned dielectric layer using dilute hydrofluoric acid, the trenches which have been introduced into the dielectric layer are widened to a significantly lesser extent than after incineration under the conditions which have previously been customary.

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